

KS54AHCT 210

KS74AHCT

Octal Buffers and Line Drivers with 3-State Outputs

T-52-07

FEATURES

- Function, pin-out, speed and drive compatibility with 54/74ALS logic family
- Low power consumption characteristic of CMOS
- High-Drive-Current outputs:
 $I_{OL} = 24\text{ mA}$ @ $V_{OL} = 0.5\text{V}$
- Inputs and outputs interface directly with TTL, NMOS and CMOS devices
- Wide operating voltage range: 4.5V to 5.5V
- Characterized for operation over industrial and military temperature ranges:
KS74AHCT: -40°C to $+85^{\circ}\text{C}$
KS54AHCT: -55°C to $+125^{\circ}\text{C}$
- Package options include plastic "small outline" packages, standard plastic and ceramic 300-mil DIPs

DESCRIPTION

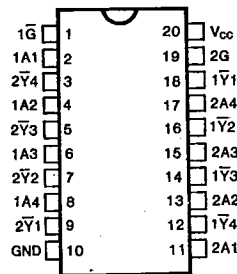
These high-speed octal buffers and line drivers are designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

The designer has the choice of combinations of inverting non-inverting outputs and symmetrical complementary input control (both active-low, or one active-low, the other active-high).

These devices provide speeds and drive capability equivalent to their ALSTTL counterparts and yet maintain CMOS power levels. The input and output voltage levels allow direct interface with TTL, NMOS and CMOS devices without any external components.

All inputs and outputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

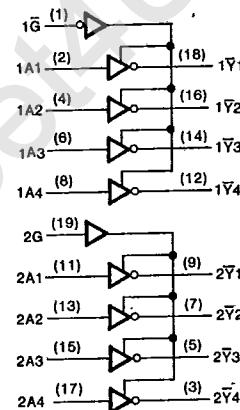
PIN CONFIGURATION



FUNCTION TABLE

Input		Output
\bar{G}	A	Y
L	L	H
L	H	L
H	X	Z

LOGIC DIAGRAM



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Absolute Maximum Ratings*

 Supply Voltage Range V_{CC} , -0.5V to +7V
 DC Input Diode Current, I_{IK}
 $(V_I < -0.5V \text{ or } V_I > V_{CC} + 0.5V)$ ± 20 mA

 DC Output Diode Current, I_{OK}
 $(V_O < -0.5V \text{ or } V_O > V_{CC} + 0.5V)$ ± 20 mA

 Continuous Output Current Per Pin, I_O
 $(-0.5V < V_O < V_{CC} + 0.5V)$ ± 70 mA

Continuous Current Through

 V_{CC} or GND pins ± 250 mA

 Storage Temperature Range, T_{stg} -65°C to +150°C

 Power Dissipation Per Package, P_d † 500 mW

* Absolute Maximum Ratings are those values beyond which permanent damage to the device may occur. These are stress ratings only and functional operation of the device at or beyond them is not implied. Long exposure to these conditions may affect device reliability.

† Power Dissipation temperature derating:

Plastic Package (N): -12mW/°C from 65°C to 85°C

Ceramic Package (J): -12mW/°C from 100°C to 125°C

Recommended Operating Conditions

 Supply Voltage, V_{CC} 4.5V to 5.5V

 DC Input & Output Voltages*, V_{IN} , V_{OUT} ... 0V to V_{CC}

Operating Temperature

Range KS74AHCT: -40°C to +85°C

KS54AHCT: -55°C to +125°C

 Input Rise & Fall Times, t_r , t_f Max 500 ns

* Unused inputs must always be tied to an appropriate logic voltage level (either V_{CC} or GND)

DC ELECTRICAL CHARACTERISTICS ($V_{CC}=5V \pm 10\%$ Unless Otherwise Specified)

Characteristic	Symbol	Test Conditions	T _a = 25°C		KS74AHCT	KS54AHCT	Unit
			Typ	Guaranteed Limits		T _a = -40°C to +85°C	
Minimum High-Level Input Voltage	V _{IH}			2.0	2.0	2.0	V
Maximum Low-Level Input Voltage	V _{IL}			0.8	0.8	0.8	V
Minimum High-Level Output Voltage	V _{OH}	V _{IN} =V _{IH} or V _{IL} I _O =-20μA I _O =-6mA	V _{CC} 4.2	V _{CC} - 0.1 3.98	V _{CC} - 0.1 3.84	V _{CC} - 0.1 3.7	V
Maximum Low-Level Output Voltage	V _{OL}	V _{IN} =V _{IH} or V _{IL} I _O =20μA I _O =12mA I _O =24mA	0	0.1 0.26 0.39	0.1 0.33 0.5	0.1 0.4	V
Maximum Input Current	I _{IN}	V _{IN} =V _{CC} or GND		±0.1	±1.0	±1.0	μA
Maximum 3-State Leakage Current	I _{OZ}	Output Enable = V _{IH} V _{OUT} =V _{CC} or GND		±0.5	±5.0	±10.0	μA
Maximum Quiescent Supply Current	I _{CC}	V _{IN} =V _{CC} or GND I _{OUT} =0μA		8.0	80.0	160.0	μA



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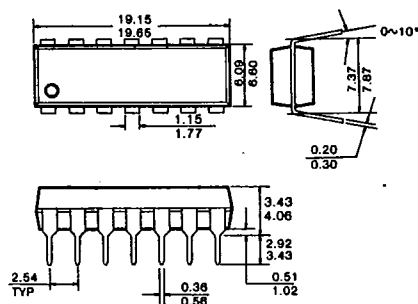
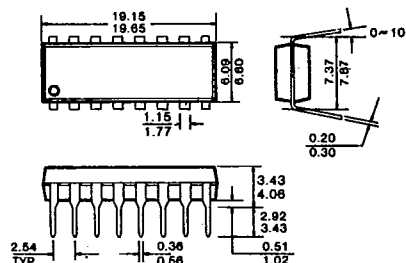
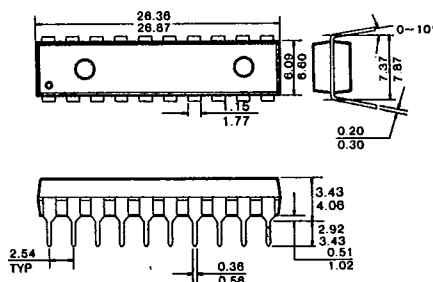
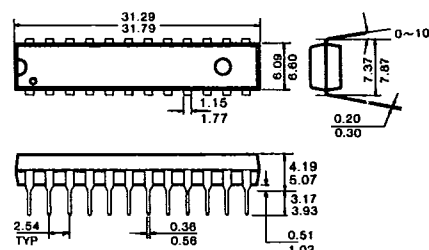
AC ELECTRICAL CHARACTERISTICS (Input $t_r, t_f \leq 2$ ns), AHCT210

Characteristic	Symbol	Conditions†	$T_a = 25^\circ\text{C}$ $V_{CC} = 5.0\text{V}$	KS74AHCT $T_a = -40^\circ\text{C to } +85^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$		KS54AHCT $T_a = -55^\circ\text{C to } +125^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$		Unit
			Typ	Min	Max	Min	Max	
Propagation Delay, A to Y	t_{PLH}	$C_L = 50\text{pF}$	6		10		12	ns
		$C_L = 150\text{pF}$	9		15		18	
	t_{PHL}	$C_L = 50\text{pF}$	7		10		12	
		$C_L = 150\text{pF}$	11		16		19	
Output Enable Time, Enable to Y	t_{PZH}	$C_L = 50\text{pF}$	12		20		24	ns
		$C_L = 150\text{pF}$	15		25		30	
	t_{PZL}	$R_L = 1\text{k}\Omega$ $C_L = 50\text{pF}$	12		20		24	
		$C_L = 150\text{pF}$	15		25		30	
Output Disable Time, Enable to Y	t_{PHZ}	$R_L = 1\text{k}\Omega$	13		18		22	ns
	t_{PLZ}	$C_L = 50\text{pF}$	13		18		22	
Input Capacitance	C_{IN}		5					pF
Output Capacitance	C_{OUT}	Output Disabled	10					pF
Power Dissipation Capacitance*	C_{PD}^*	Output Disabled	5					pF
		Output Enabled	30					

* C_{PD} determines the no-load dynamic power dissipation: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

† For AC switching test circuits and timing waveforms see section 2.



PACKAGE DIMENSIONS*T-90-20***1. PLASTIC PACKAGES****14-Pin Plastic DIP Units: mm****16-Pin Plastic DIP Units: mm****20-Pin Plastic DIP Units: mm****24-Pin Plastic DIP Units: mm**

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**SAMSUNG SEMICONDUCTOR**

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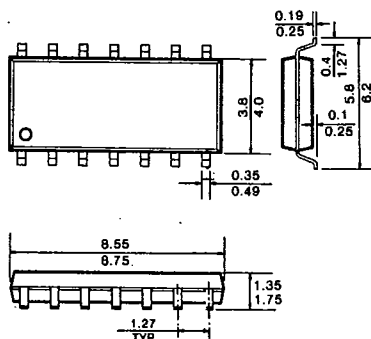
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PACKAGE DIMENSIONS

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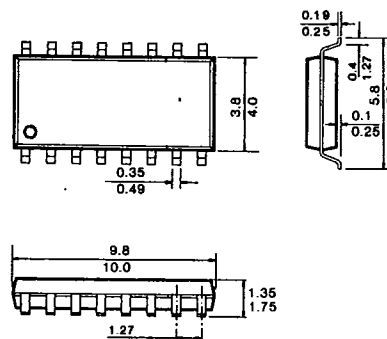
14-Pin SOP

Unit: mm



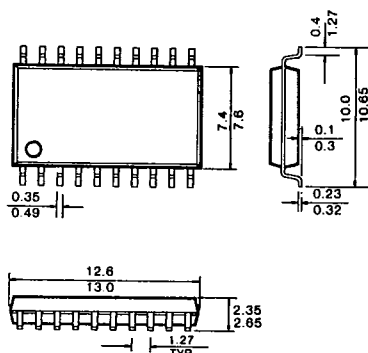
16-Pin SOP

Unit: mm



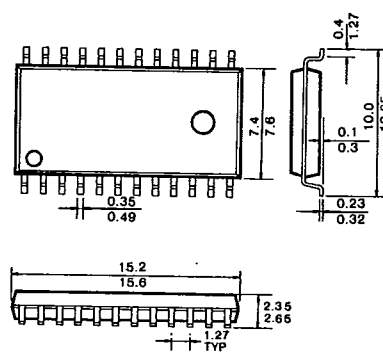
20-Pin SOP

Unit: mm



24-Pin SOP

Unit: mm



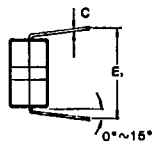
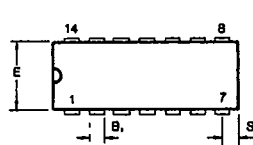
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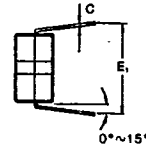
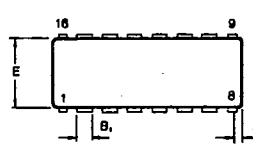
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PACKAGE DIMENSIONS

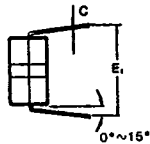
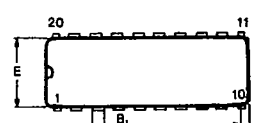
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2. CERAMIC PACKAGES**14-Pin Ceramic DIP Units: mm**

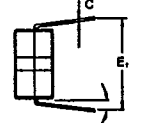
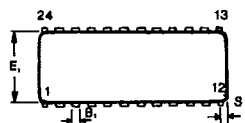
DIM	Millimeters	
	Min	Max
A	—	5.08
B	0.38	0.58
B ₁	1.40	1.78
C	0.20	0.38
D	18.16	19.56
E	8.10	7.49
E ₁	7.62	10.03
F	2.54	
L	3.18	4.19
Q	0.51	1.02
S	1.91	2.29

16-Pin Ceramic DIP Units: mm

DIM	Millimeters	
	Min	Max
A	—	5.08
B	0.38	0.58
B ₁	1.40	1.78
C	0.20	0.38
D	19.05	19.94
E	8.10	7.49
E ₁	7.62	10.03
F	2.54	
L	3.18	4.19
Q	0.51	1.02
S	0.51	1.14

20-Pin Ceramic DIP Units: mm

DIM	Millimeters	
	Min	Max
A	4.06	5.08
B	0.38	0.53
B ₁	1.14	1.52
C	0.20	0.38
D	25.78	26.93
E	8.10	8.60
E ₁	7.77	7.98
F	2.54	
L	3.73	4.01
Q	0.38	0.89
S	0.51	1.14

24-Pin Ceramic DIP Units: mm

DIM	Millimeters	
	Min	Max
A	4.06	5.08
B	0.38	0.53
B ₁	1.14	1.52
C	0.20	0.38
D	31.50	32.84
E	7.24	7.75
E ₁	7.77	7.98
F	2.54	
L	3.73	4.01
Q	0.508	1.778
S	1.85	1.93



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